

# RJK1560DPP-M0

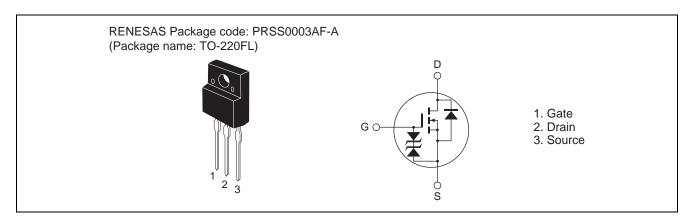
# Silicon N Channel MOS FET High Speed Power Switching

R07DS0270EJ0100 Rev.1.00 Mar 07, 2011

#### **Features**

- Capable of 2.5 V gate drive
- Low on-resistance  $R_{DS(on)}=0.043~\Omega~typ.~(at~I_D=10~A,~V_{GS}=4~V,~Ta=25^{\circ}C)$
- Low leakage current
- High speed switching

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                       | Ratings     | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>             | 150         | V    |
| Gate to source voltage                      | V <sub>GSS</sub>             | ±10         | V    |
| Drain current                               | I <sub>D</sub>               | 20          | Α    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1 | 80          | Α    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>              | 20          | Α    |
| Body-drain diode reverse drain peak current | I <sub>DR</sub> (pulse)      | 80          | Α    |
| Avalanche current                           | I <sub>AP</sub> Note3        | 16          | Α    |
| Avalanche energy                            | E <sub>AR</sub> Note3        | 19.2        | mJ   |
| Channel dissipation                         | Pch Note2                    | 28.5        | W    |
| Channel to case thermal impedance           | θch-c                        | 4.38        | °C/W |
| Channel temperature                         | Tch                          | 150         | °C   |
| Storage temperature                         | Tstg                         | −55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at  $Tc = 25^{\circ}C$
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

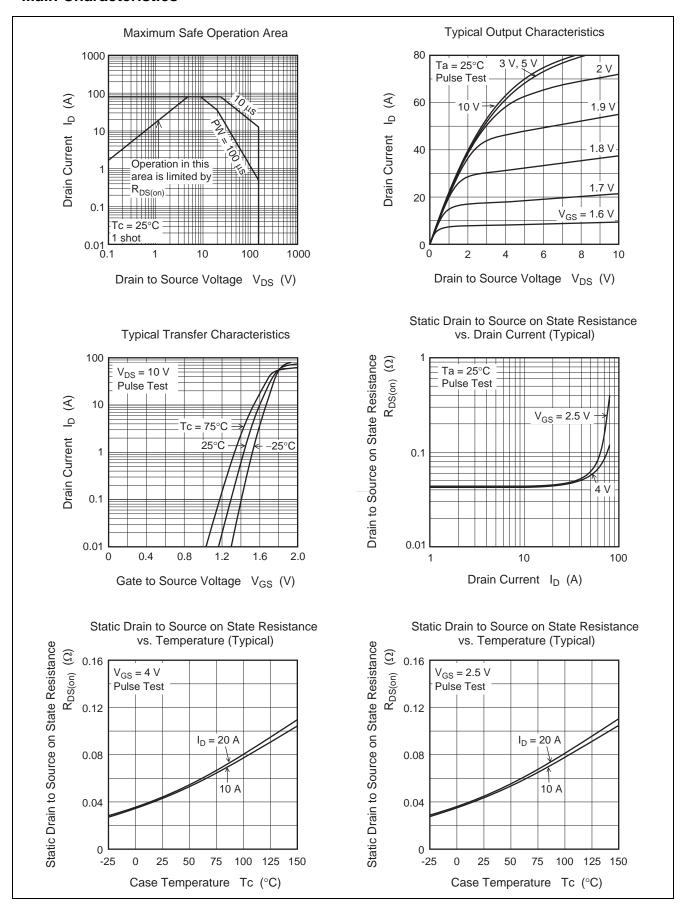
# **Electrical Characteristics**

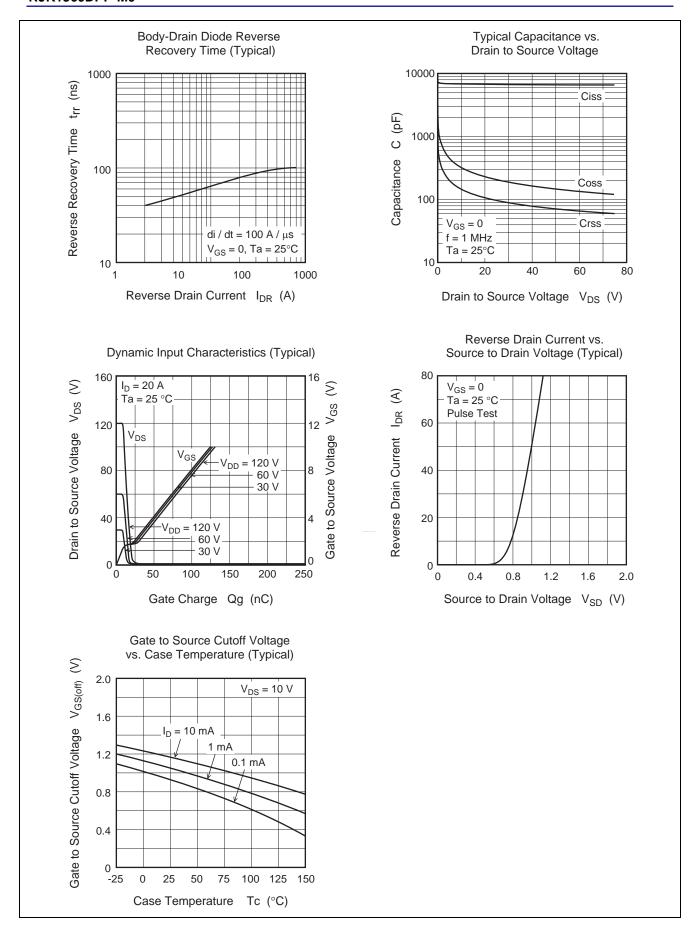
 $(Ta = 25^{\circ}C)$ 

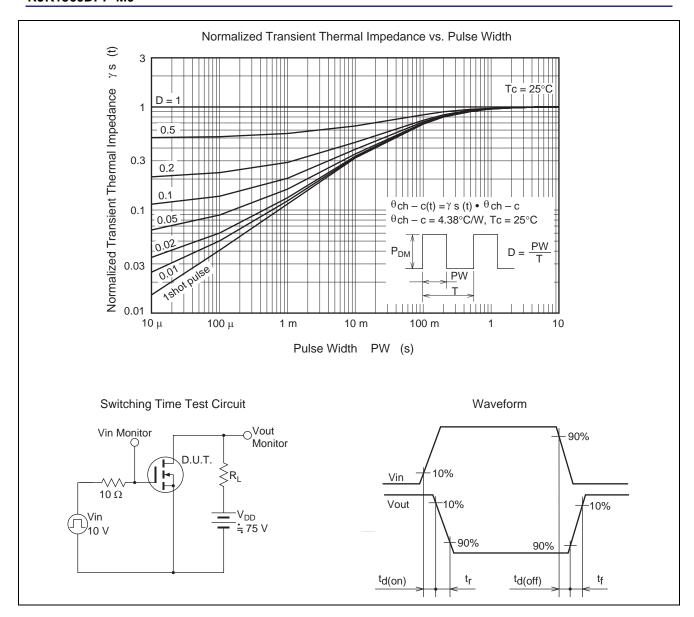
| Item                                   | Symbol              | Min | Тур   | Max   | Unit | Test conditions   |
|--|---------------------|-----|-------|-------|------|---|
| Drain to source breakdown voltage      | $V_{(BR)DSS}$       | 150 | _     | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$   |
| Gate to source breakdown voltage       | $V_{(BR)GSS}$       | ±10 | _     | _     | V    | $I_G = \pm 100 \ \mu A, \ V_{DS} = 0$                                     |
| Zero gate voltage drain current        | I <sub>DSS</sub>    | _   | _     | 1     | μΑ   | $V_{DS} = 150 \text{ V}, V_{GS} = 0$                                      |
| Gate to source leak current            | I <sub>GSS</sub>    | _   | _     | ±10   | μΑ   | $V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$                                   |
| Gate to source cutoff voltage          | $V_{GS(off)}$       | 0.5 | _     | 1.5   | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                             |
| Static drain to source on state        | R <sub>DS(on)</sub> | _   | 0.043 | 0.060 | Ω    | $I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note4}}$                 |
| resistance                             | R <sub>DS(on)</sub> | _   | 0.044 | 0.070 | Ω    | $I_D = 10 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note4}}$               |
| Input capacitance                      | Ciss                | _   | 6720  | _     | pF   | V <sub>DS</sub> = 25 V  |
| Output capacitance                     | Coss                | _   | 205   | _     | pF   | $V_{GS} = 0$  |
| Reverse transfer capacitance           | Crss                | _   | 102   | _     | pF   | f = 1 MHz   |
| Turn-on delay time                     | t <sub>d(on)</sub>  | _   | 43    | _     | ns   | I <sub>D</sub> = 10 A   |
| Rise time                              | t <sub>r</sub>      | _   | 79    | _     | ns   | $V_{GS} = 4 V$  |
| Turn-off delay time                    | t <sub>d(off)</sub> | _   | 250   | _     | ns   | $R_{L} = 7.5 \Omega$ $Rg = 10 \Omega$                                     |
| Fall time                              | t <sub>f</sub>      | _   | 117   | _     | ns   |   |
| Total gate charge                      | Qg                  | _   | 52    | _     | nC   | V <sub>DD</sub> = 120 V   |
| Gate to source charge                  | Qgs                 | _   | 13    | _     | nC   | V <sub>GS</sub> = 4 V<br>I <sub>D</sub> = 20 A                            |
| Gate to drain charge                   | Qgd                 | _   | 14    | _     | nC   |   |
| Body-drain diode forward voltage       | $V_{DF}$            | _   | 0.83  | 1.30  | V    | I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 Note4                          |
| Body-drain diode reverse recovery time | t <sub>rr</sub>     | _   | 75    | _     | ns   | $I_F = 20 \text{ A}, V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 4. Pulse test

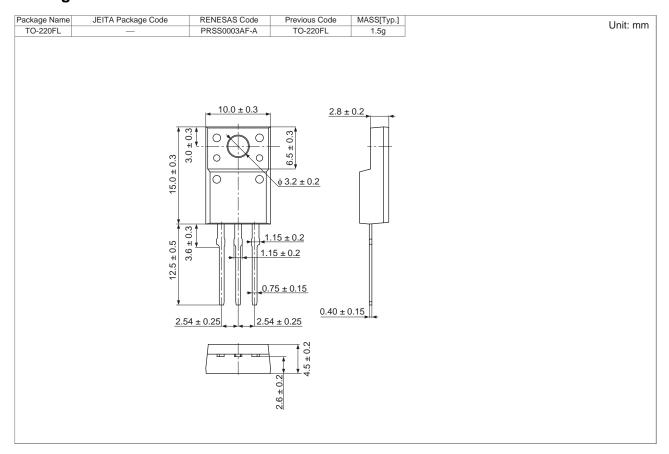
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK1560DPP-M0-T2      | 600 pcs  | Box (Tube)         |

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